



Docket No.: GR 98 P 2499 P

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By: 

Date: May 14, 2001

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Thomas Peter Haneder et al.
Appl. No. : 09/801,209
Filed : March 7, 2001
Title : Ferroelectric Transistor, Use Therof in a Memory Cell Configuration
and Method of Producing the Ferroelectric Transistor
Art Unit :

LETTER

Hon. Commissioner of Patents and Trademarks,
Washington, D.C. 20231

Sir:

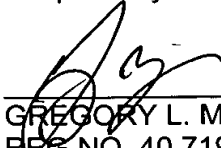
The above-mentioned new patent application was filed on March 7, 2001 without a signed oath or declaration, under the provision of 37 C.F.R. 1.53(f).

In accordance with the above-mentioned rule, enclosed herewith is the original signed declaration.

The undersigned hereby states that the application filed in the Patent and Trademark Office is the application which the inventor(s) executed by signing the declaration. MPEP 601.01(a).

The fee required for the late filing of an oath or declaration in the amount of \$130.00 is also enclosed.

Respectfully submitted,



GREGORY L. MAYBACK
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/mjb

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